

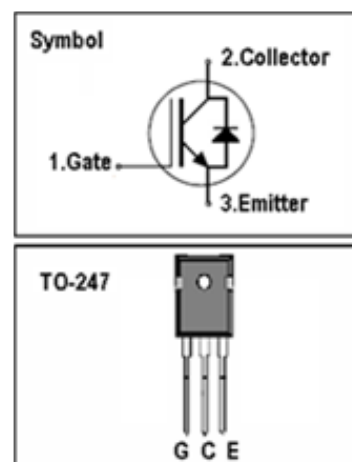
IGBT

Features

- 1200V,25A
- $V_{CE(sat)}(typ.)=1.7V@V_{GE}=15V, I_C=25A$
- High speed switching
- Higher system efficiency
- Soft current turn-off waveforms
- Square RBSOA

General Description

JIAEN Trench IGBTs offer lower losses and higher energy efficiency for application such as Motor control, general inverter and other soft switching applications.



Absolute Maximum Ratings

Symbol	Parameter	Value	Units
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Continuous Collector Current ($T_C=25^\circ C$)	50	A
	Continuous Collector Current ($T_C=100^\circ C$)	25	A
I_{CM}	Pulsed Collector Current (Note 1)	100	A
I_F	Diode Continuous Forward Current ($T_C=100^\circ C$)	25	A
I_{FM}	Diode Maximum Forward Current (Note 1)	100	A
t_{sc}	Short Circuit Withstand Time	10	us
P_D	Maximum Power Dissipation ($T_C=25^\circ C$)	428	W
	Maximum Power Dissipation ($T_C=100^\circ C$)	214	W
T_J	Operating Junction Temperature Range	-40 to +175	$^\circ C$
T_{STG}	Storage Temperature Range	-55 to +150	$^\circ C$

Thermal Characteristics

Symbol	Parameter	Max.	Units
$R_{th j-c}$	Thermal Resistance, Junction to case for IGBT	0.35	$^\circ C/W$
$R_{th j-c}$	Thermal Resistance, Junction to case for Diode	0.9	$^\circ C/W$
$R_{th j-a}$	Thermal Resistance, Junction to Ambient	40	$^\circ C/W$

Electrical Characteristics (T_C=25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{CES}	Collector-Emitter Breakdown Voltage	V _{GE} = 0V, I _C = 250uA	1200	-	-	V
I _{CES}	Collector-Emitter Leakage Current	V _{CE} = 1200V, V _{GE} = 0V	-	-	250	uA
I _{GES}	Gate Leakage Current, Forward	V _{GE} = ± 20V, V _{CE} = 0V	-	-	± 100	nA
V _{GE(th)}	Gate Threshold Voltage	V _{GE} = V _{CE} , I _C =1mA	5.8	6.1	6.3	V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	V _{GE} =15V, I _C = 25A	-	1.7		V
Q _g	Total Gate Charge	V _{CC} =960V V _{GE} =15V I _C =25A	-	133		nC
t _{d(on)}	Turn-on Delay Time	V _{CC} =600V V _{GE} =15V I _C =25A R _G =10Ω Inductive Load T _C =25 °C	-	31	-	ns
t _r	Turn-on Rise Time		-	62	-	ns
t _{d(off)}	Turn-off Delay Time		-	184	-	ns
t _f	Turn-off Fall Time		-	59	-	ns
E _{on}	Turn-on Switching Loss		-	2.0	-	mJ
E _{off}	Turn-off Switching Loss		-	0.9	-	mJ
E _{ts}	Total Switching Loss		-	2.9	-	mJ
C _{ies}	Input Capacitance	V _{CE} =30V	-	2080	-	pF
C _{oes}	Output Capacitance	V _{GE} =0V	-	105	-	pF
C _{res}	Reverse Transfer Capacitance	f = 1MHz	-	20	-	pF

Electrical Characteristics of Diode (T_C=25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _F	Diode Forward Voltage	I _F =25A	-	2.0	-	V
t _{rr}	Diode Reverse Recovery Time	V _{CE} = 600V	-	309	-	ns
I _{rr}	Diode peak Reverse Recovery Current	I _F = 25A	-	7	-	A
Q _{rr}	Diode Reverse Recovery Charge	dI _F /dt = 250A/us	-	1038	-	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature

Typical Performance Characteristics

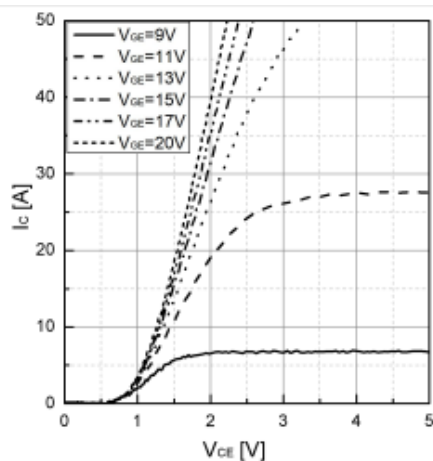


Fig 1. Typical output characteristic ($T_{vj}=25^{\circ}\text{C}$)

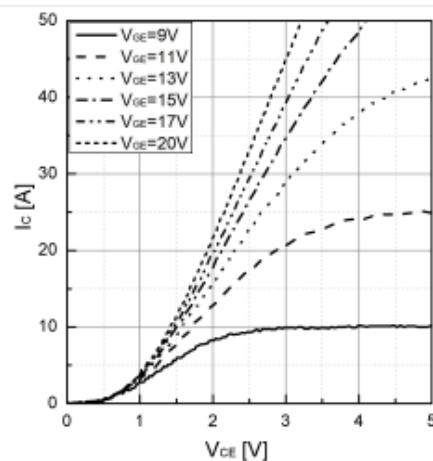


Fig 2. Typical output characteristic ($T_{vj}=175^{\circ}\text{C}$)

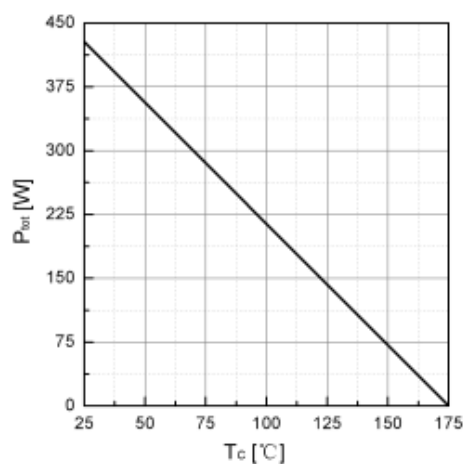


Fig 3. Power dissipation as a function of T_c

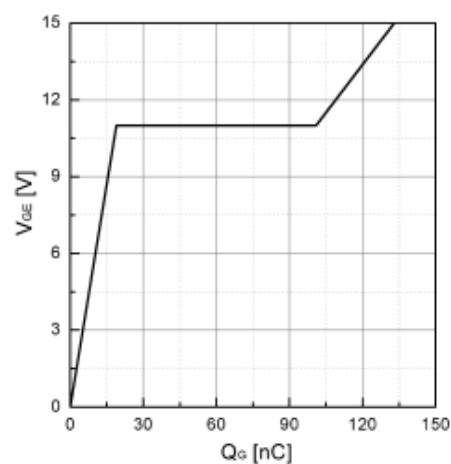


Fig 4. Typical Gate charge

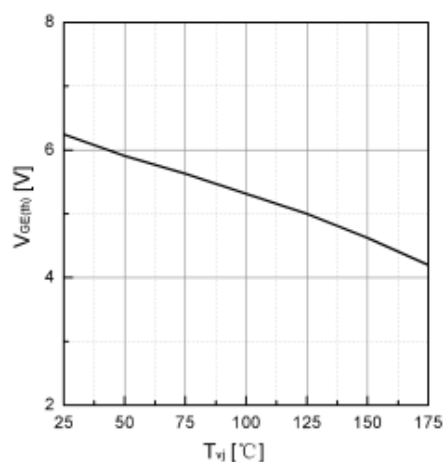


Fig 5. Typical $V_{GE(th)}$ as a function of T_{vj}
($I_c=1\text{mA}$)

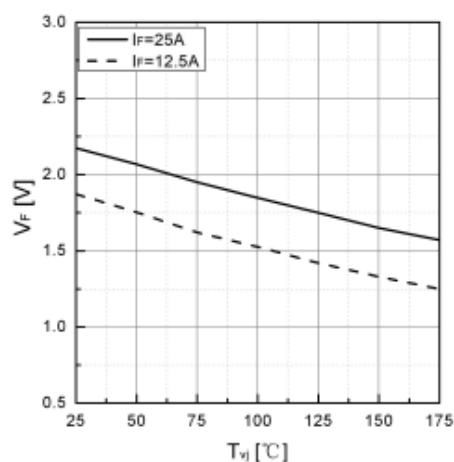


Fig 6. Typical V_F as a function of T_{vj}

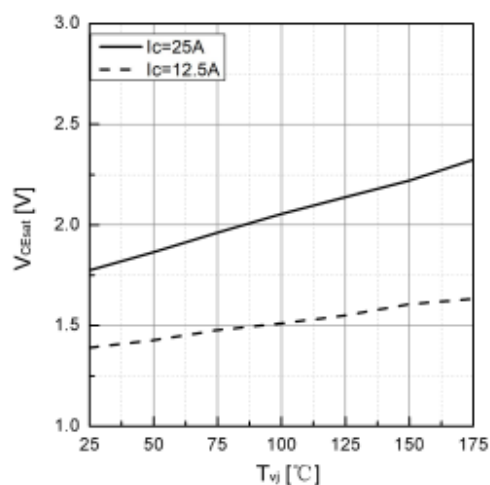


Fig 7. Typical V_{CEsat} as a function of T_{vj}

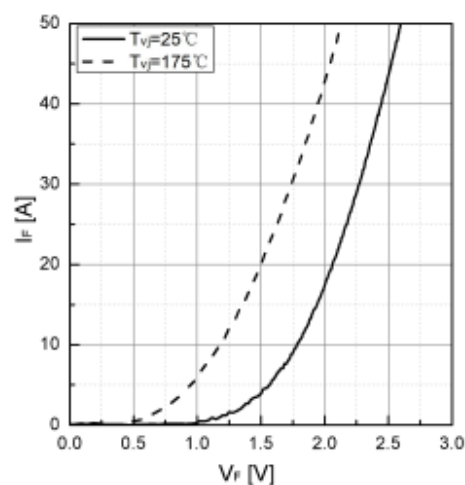


Fig 8. Typical I_F as a function of V_F

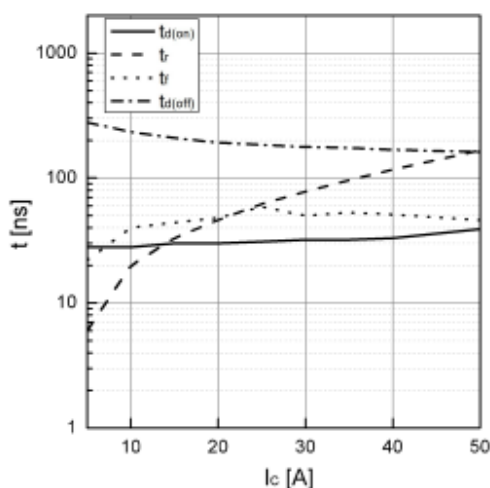


Fig 9. Typical switching time as a function of I_C

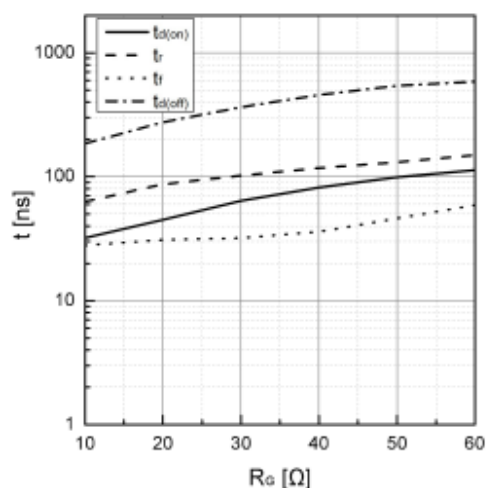


Fig 10. Typical switching times as a function of R_G

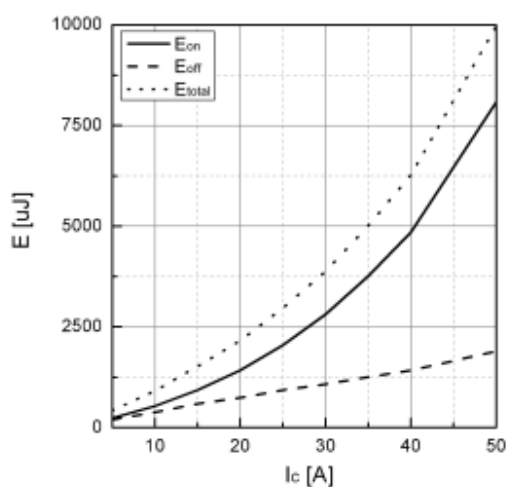


Fig 11. Typical switching energy losses as a function of I_C

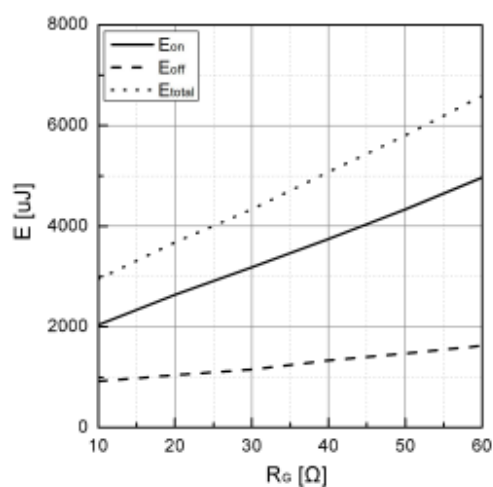


Fig 12. Typical switching energy losses as a function of R_G

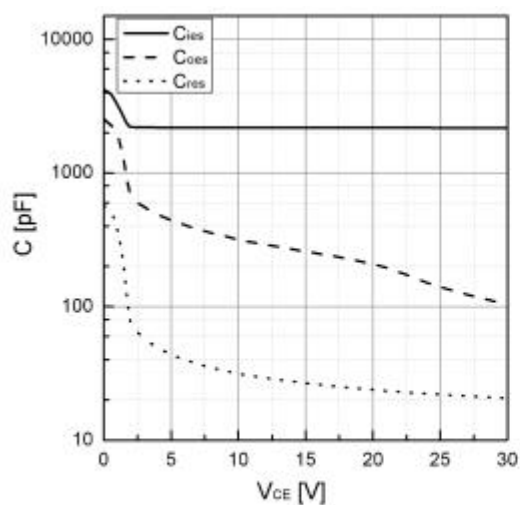


Fig 13. Typical capacitance as a function of V_{CE}
($f=1\text{MHz}$, $V_{GE}=0\text{V}$)

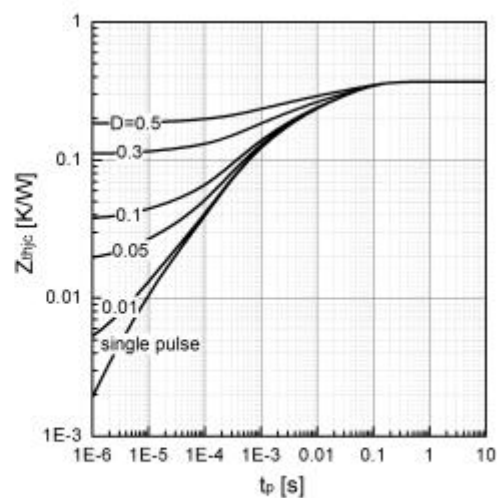
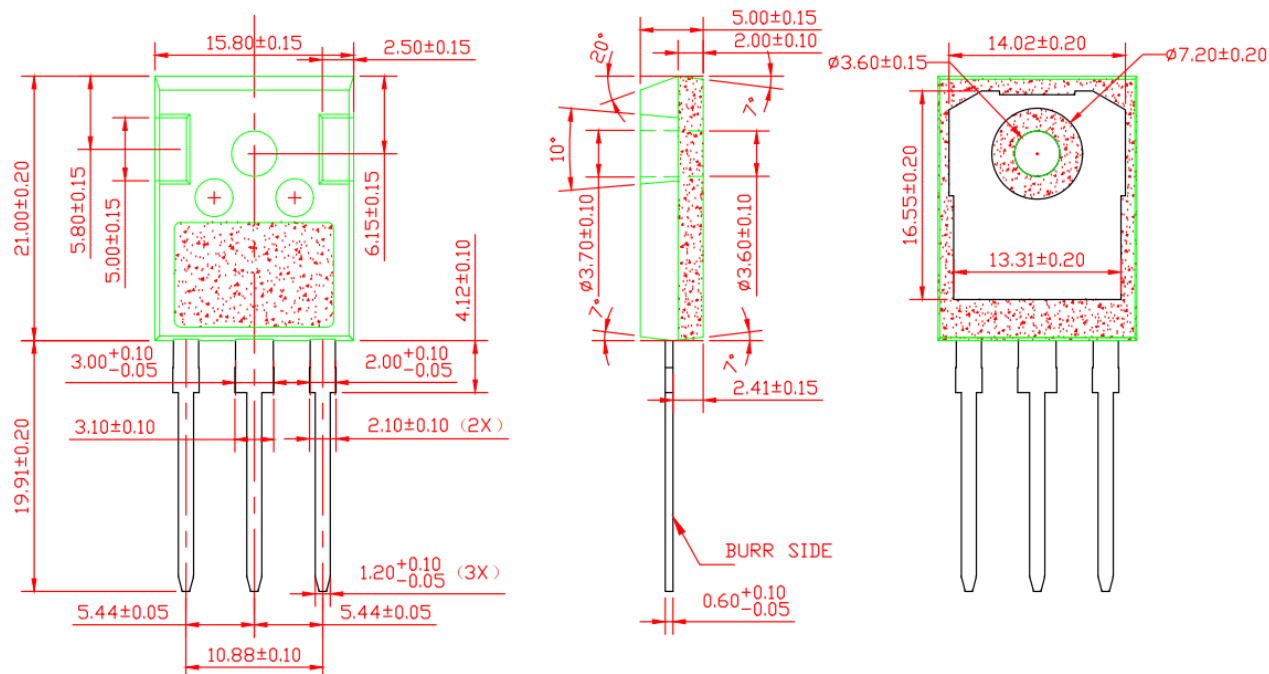


Fig 14. Transient thermal impedance of IGBT

TO-247 PACKAGE OUTLINE



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